



#1/10/02
PATENT
0465-0884R
11/12/02

IN THE U.S. PATENT AND TRADEMARK OFFICE

Applicant: PARK, Ji Soo et al. Conf.: 5713
Appl. No.: 09/998,131 Group: 2825
Filed: December 3, 2001 Examiner: B. KESHAVAN
For: SEMICONDUCTOR DEVICE HAVING A GATE AND
FABRICATION METHOD THEREFOR

AMENDMENT

Honorable Commissioner of Patents
Washington, D.C. 20231

November 12, 2002

Sir:

In response to the Examiner's Office Action dated August 12, 2002, the following amendments and remarks are respectfully submitted in connection with the above-identified application.

In the Claims:

Please amend the claims as follows:

1. (Amended) A method for forming a gate in a semiconductor device,
comprising:

forming a first insulating film and a non-silicide conductive film on a
semiconductor substrate;

patterning the first insulating film and the conductive film, to form a
gate, wherein the top and side surfaces of said gate are exposed;

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- ☐ Petition for () month(s) extension of time pursuant to 37 C.F.R. §§ 1.17 and 1.136(a). \$0.00 for the extension of time.
- ☒ No fee is required.
- ☐ Check(s) in the amount of \$0.00 is(are) enclosed.
- ☐ Please charge Deposit Account No. 02-2448 in the amount of \$0.00. This form is submitted in triplicate.

If necessary, the Commissioner is hereby authorized in this, concurrent, and future replies, to charge payment or credit any overpayment to Deposit Account No. 02-2448 for any additional fees required under 37 C.F.R. § 1.16 or under 37 C.F.R. § 1.17; particularly, extension of time fees.

Respectfully submitted,

BIRCH, STEWART, KOLASCH & BIRCH, LLP

By 

Joseph A. Kolasch, #22,463


JAK/PLS/asc
0465-0881P

P.O. Box 747
Falls Church, VA 22040-0747
(703) 205-8000

Attachment(s)

(Rev. 10/15/02)